1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61003PY

2. Features and benefits

- · High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- · Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Loadswitch
- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
Ic	collector current		-	-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	8	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 50 mA; $t_p \le 300$ μs; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	90	150	mΩ
		I_C = 3 A; I_B = 300 mA; $t_p \le$ 300 μs; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	75	110	mΩ



100 V, 3 A NPN high power bipolar transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	С
2	E	emitter	<u> </u>	
3	Е	emitter	a	B —
4	В	base		Ė
mb	С	collector	1 2 3 4	sym123
			LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT61003NY	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61003NY	1003NAB

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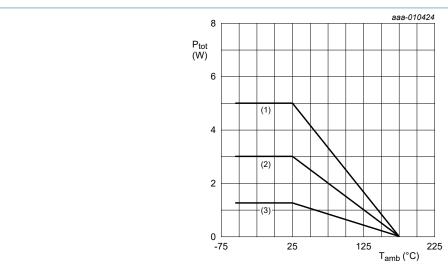
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	100	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
Ic	collector current			-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	Α
I _B	base current			-	0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB) single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

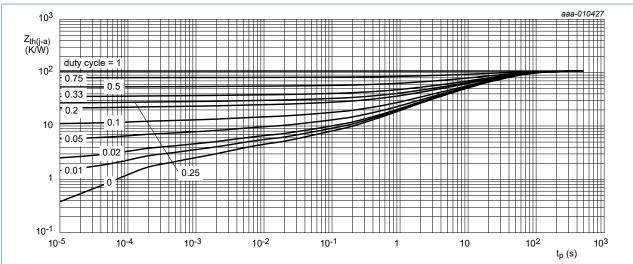
100 V, 3 A NPN high power bipolar transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from		[1]	-	-	115	K/W
	junction to ambient		[2]	-	-	50	K/W
			[3]	-	-	30	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

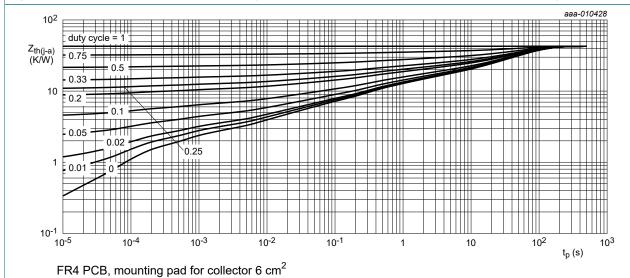


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

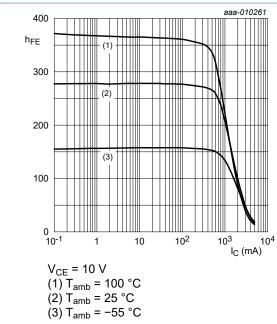
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 500 mA; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	150	250	-	
		V_{CE} = 10 V; I_{C} = 1 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	80	250	-	
		V_{CE} = 10 V; I_{C} = 2 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pused	20	100	-	
		V_{CE} = 10 V; I_{C} = 3 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	10	40	-	
OLOGI	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; $t_p \le 300 \mu s$; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	90	150	mV
		I_C = 3 A; I_B = 300 mA; t_p ≤ 300 μs; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	225	330	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 50 mA; $t_p \le 300 \mu s$; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	90	150	mΩ
		I_C = 3 A; I_B = 300 mA; $t_p \le$ 300 μs; pulsed; $\delta \le$ 0.02; T_{amb} = 25 °C	-	75	110	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; $t_p \le 300 \mu s$; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	0.86	1	V
		I_C = 2 A; I_B = 200 mA; $t_p \le 300 \ \mu s$; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	1	1.2	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 0.1 A; T _{amb} = 25 °C	-	0.67	0.85	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A;	-	20	-	ns
t _r	rise time	I _{Boff} = -0.05 A; T _{amb} = 25 °C	-	300	-	ns
t _{on}	turn-on time		-	320	-	ns
s	storage time		-	830	-	ns
t _f	fall time		-	470	-	ns
t _{off}	turn-off time	[-	1300	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	11	-	pF

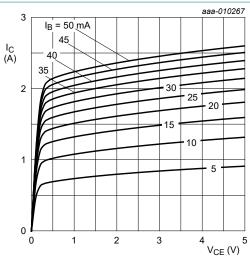
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$$(1) T_{amb} = 100 °($$

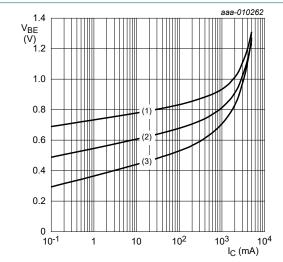
(2)
$$I_{amb} = 25 ^{\circ} C$$

Fig. 4. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



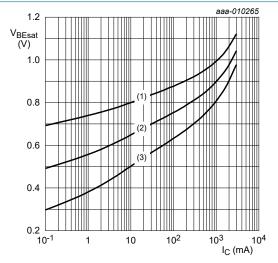
$$V_{CE}$$
 = 2 V

$$(1) T_{amb} = -55 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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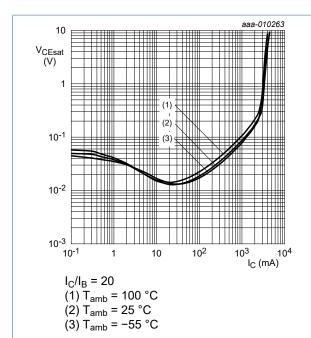


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

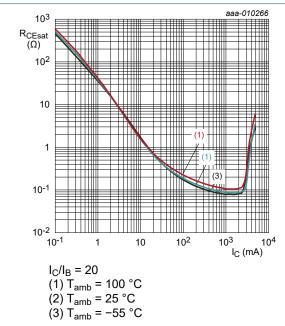


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

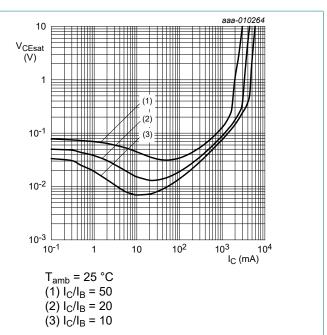


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

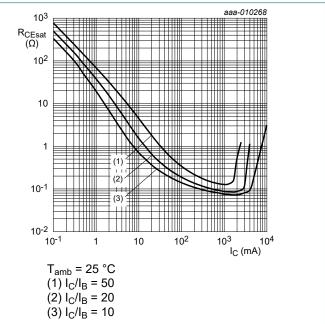
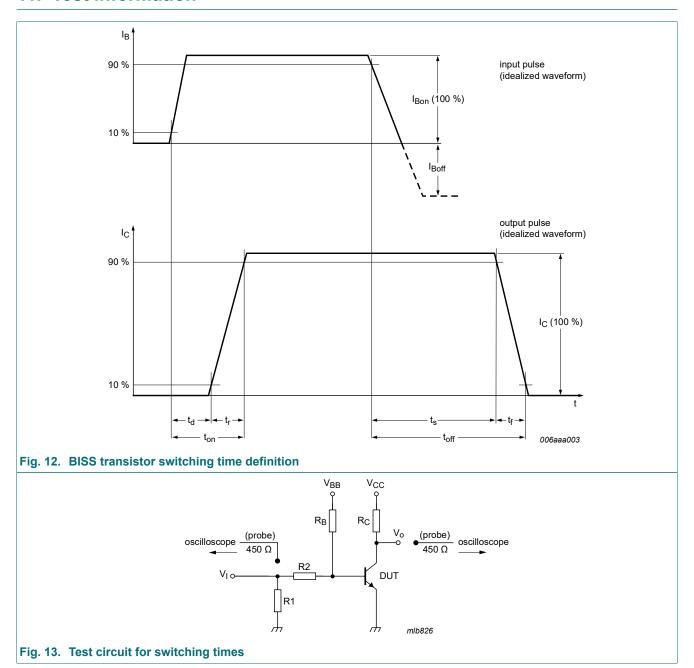


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

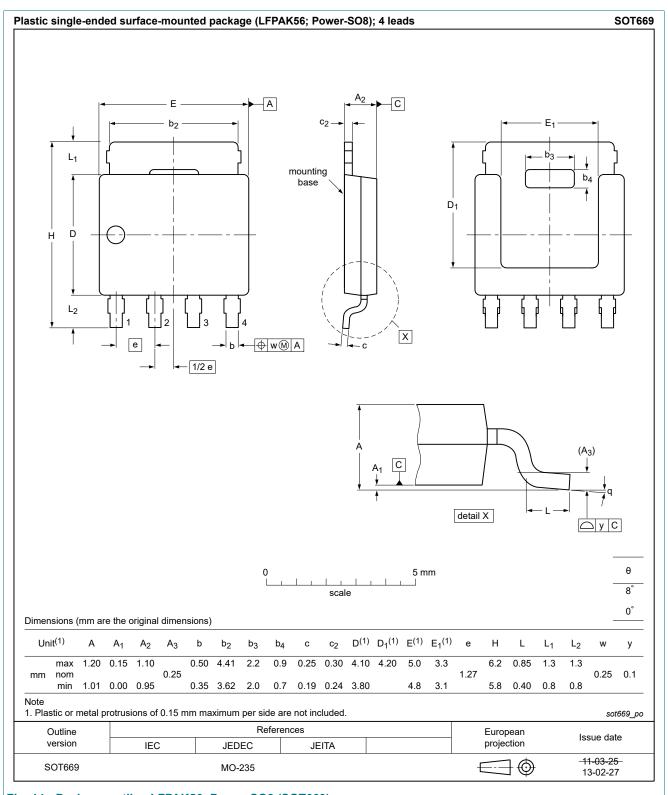
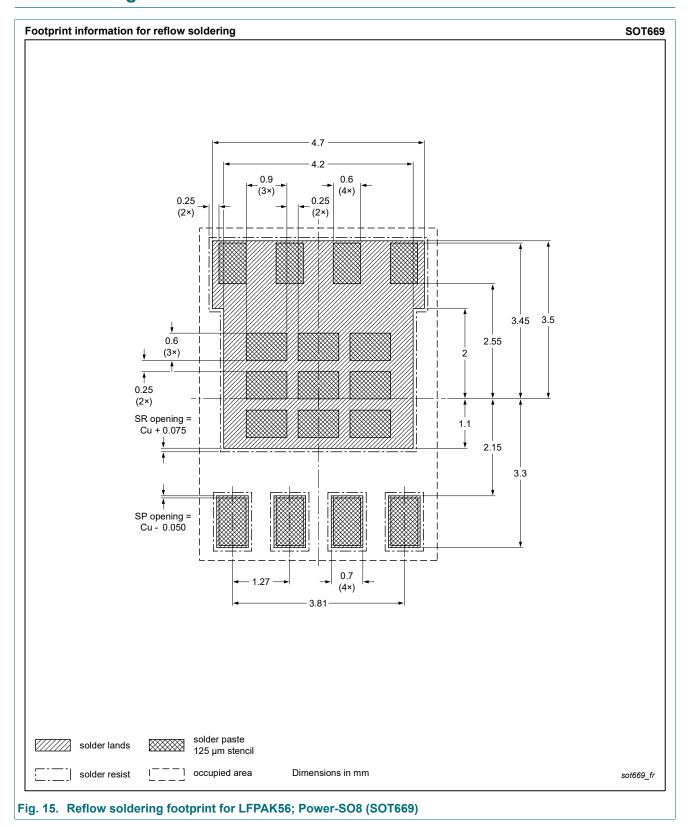


Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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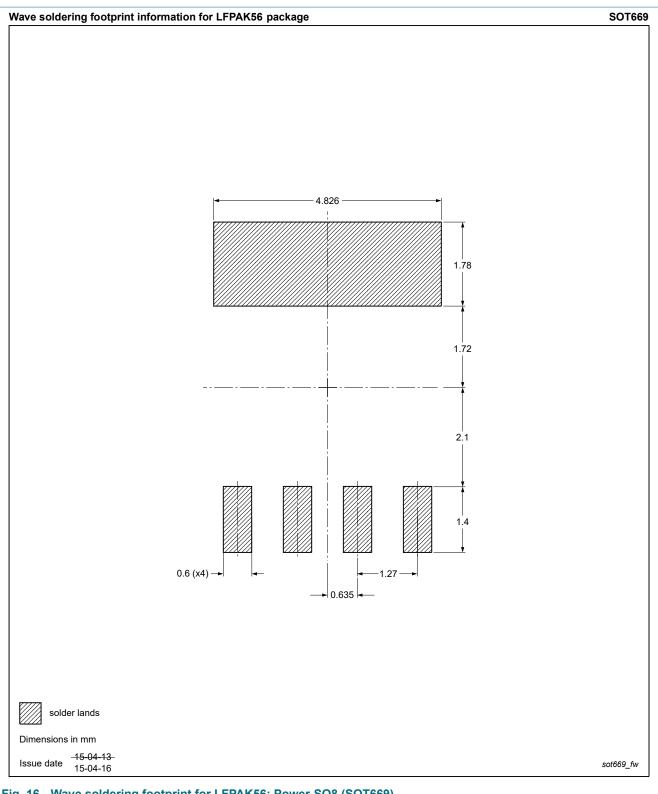


Fig. 16. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

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14. Revision history

Table 8. Revision history

	•			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61003NY v.5	20200910	Product data sheet	-	PHPT61003NY v.4
Modifications:	Characteristics: Figu	res 6, 7, 8 and 10 correct	ed	
PHPT61003NY v.4	20150911	Product data sheet	-	PHPT61003NY v.3
PHPT61003NY v.3	20140113	Product data sheet	-	PHPT61003NY v.2
PHPT61003NY v.2	20140109	Product data sheet	-	PHPT61003NY v.1
PHPT61003NY v.1	20131213	Product data sheet	-	

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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PHPT61003NY

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